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CORRECTION

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Correction: The polarization-dependent anisotropic Raman response of few-layer and bulk WTe_2 under different excitation wavelengths

Qingjun Song,[ab] Haifeng Wang,[cd] Xiaolong Xu,[ab] Xingchen Pan,[cd] Yilun Wang,[ab] Fengqi Song,[cd] Xiangang Wan*[cd] and Lun Dai*[ab]

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Correction for 'The polarization-dependent anisotropic Raman response of few-layer and bulk WTe_2 under different excitation wavelengths' by Qingjun Song *et al.*, *RSC Adv.*, 2016, **6**, 103830–103837.

In part (d) of Fig. 4 of the original manuscript, and in the description of part (d) in the Fig. 4 caption, the wrong labels were given for the modes. The labels "B_g" and "A_u" should be "B_u" and "A_g", respectively. The corrected Fig. 4 and its caption are shown below:

Additionally, in the Results and Discussion section, in the text below Fig. 4, two sentences should be revised as follows:

"For $E_{las} \approx 2.3$ eV, the excited electron will transit from the A_g valence band to A_u conductance band, and the corresponding polar plot is shown in Fig. 4(e), where the maximum (minimum) absorption corresponds to the perpendicular (parallel) relation between the incident polarization and *a*-axis".

"To study the influence of electron–photon interaction on the anisotropic Raman scattering, we first assume the electron–phonon interaction (H_{e-ph}) in the Raman scattering is not polarization dependent".

[a]*State Key Lab for Mesoscopic Physics, School of Physics, Peking University, Beijing 100871, China. E-mail: lundai@pku.edu.cn*
[b]*Collaborative Innovation Center of Quantum Matter, Beijing 100871, China*
[c]*National Laboratory of Solid State Microstructures, College of Physics, Nanjing University, Nanjing 210093, China. E-mail: xgwan@nju.edu.cn*
[d]*Collaborative Innovation Center of Advanced Microstructures, Nanjing University, Nanjing 210093, China*

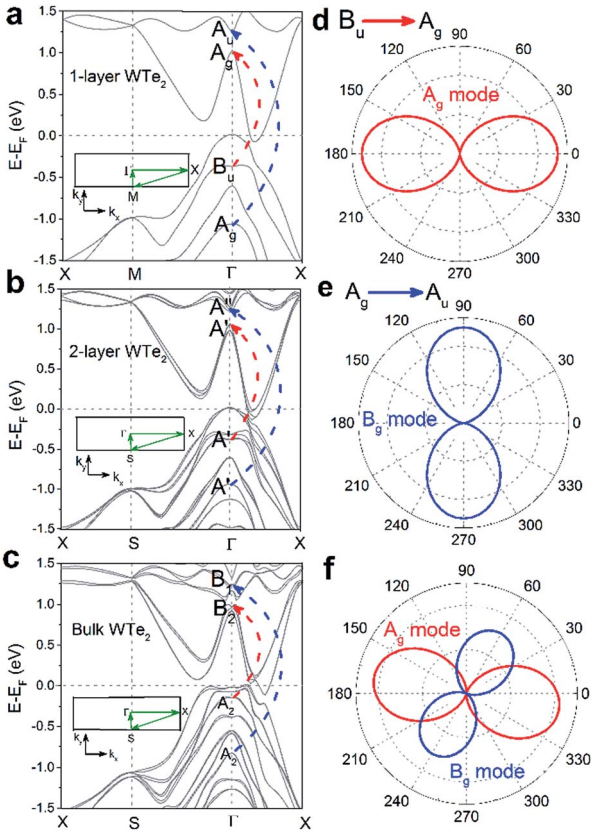

Fig. 4 (a–c) The calculated band structures of monolayer, bilayer and bulk WTe_2, respectively. The representative band symmetries at Γ point are labelled, and the insets are their 2D Brillouin zones. Calculated polarization dependence of the optical transition probability (d) from the B_u to A_g ($E_{las} \approx 1.5$ eV) and (e) from the A_g to A_u ($E_{las} \approx 2.3$ eV) in monolayer WTe_2, as indicated in (a). 0° corresponds to the W–W chain (*a*-axis) direction, the initial incident polarization and scattered polarization are along the *a*-axis ($\theta_0 = 0°$). (f) The representative calculated polarization dependent intensities of A_g and B_g modes in monolayer WTe_2 with certain θ_0 (~15°).

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.